AMENDMENTS TO THE SPECIFICATION

Please replace the paragraph beginning on page 1, line 6 with the following amended paragraph:

This application is related to U.S. Application No. 10/080,012, filed February 20, 2002, which is herein incorporated in its entirety by reference. ~~Chang et al., co-filed U.S. patent application Ser. No.: _____.attorney docket No.:CDDC/CHC/002. To the extent not repeated herein, the contents of Cheng et al., are incorporated herein by reference.~~

Please add the following new paragraph before the paragraph beginning on page 7, line 24:

Fig. 5 is a cross-sectional structural view of another embodiment of the core of an electron-emitting device provided with a seed layer in accordance with the present invention.

Please replace the paragraph beginning on page 10, line 30 with the following amended paragraph:

Fig. 3A depicts a partial cross-sectional representation of the field emitter structure 1 of one embodiment of the present invention. The method of fabricating the field emitter structure 1 generally includes providing a [[bas]] base plate 100 and disposing thereon a plurality of emitter electrodes. The group of generally parallel emitter electrodes 110 are situated on base plate ~~baseplate~~ 100.

Please replace the paragraph beginning on page 16, line 17 with the following amended paragraph:

Fig. 5 illustrates an embodiment of the invention in which the dielectric layer comprises a dual layer. As Fig. 5 illustrates ~~In one embodiment of the present invention~~, the dielectric strips 152 comprises two layers 126 and 127, which in one embodiment are formed of silicon dioxide and silicon nitride having a thickness of 0.5 – 2.0 μm. In another embodiment, dielectric layer

~~strips~~ 125 comprises ~~comprise of~~ a single layer of silicon-oxy-nitride having a thickness of 0.5 – 2.0 μm.